Silicon NPN Power Transistors 2SC3423

DESCRIPTION

・With TO-126 package
・Complement to type 2SA1360
・High transition frequency

APPLICATIONS

・Audio frequency amplifier applications

PINNING

PIN	DESCRIPTION
1	Emitter
2	Collector;connected to mounting base
3	Base

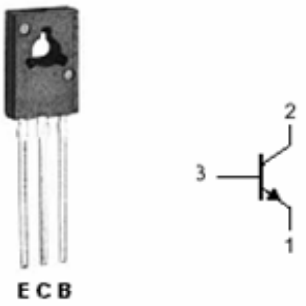

Fig.1 simplified outline (TO-126) and symbol

Absolute maximum ratings(Ta=25℃)

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
V_{CBO}	Collector-base voltage	Open emitter	150	V
V_{CEO}	Collector-emitter voltage	Open base	150	V
V_{EBO}	Emitter-base voltage	Open collector	5	V
I_C	Collector current		50	mA
I_B	Base current		5	mA
P_D	Total power dissipation	T_a=25℃	1.2	W
		T_C=25℃	5	
T_j	Junction temperature		150	℃
T_{stg}	Storage temperature		-55～+150	℃

Silicon NPN Power Transistors 2SC3423

CHARACTERISTICS

Tj=25℃ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
$V_{(BR)CEO}$	Collector-emitter breakdown voltage	I_C=1mA ;I_B=0	150			V
V_{CEsat}	Collector-emitter saturation voltage	I_C=10mA; I_B=1mA			1.0	V
V_{BE}	Base-emitter on voltage	I_C=10mA ; V_{CE}=5V			0.8	V
I_{CBO}	Collector cut-off current	V_{CB}=150V; I_E=0			0.1	μA
I_{EBO}	Emitter cut-off current	V_{EB}=5V; I_C=0			0.1	μA
h_{FE}	DC current gain	I_C=10mA ; V_{CE}=5V	80		240	
C_{ob}	Output capacitance	I_E=0 ; V_{CB}=10V f=1MHz		1.8		pF
f_T	Transition frequency	I_C=10mA ; V_{CE}=5V		200		MHz

◆ **h_{FE} Classifications**

O	Y
80-160	120-240

Silicon NPN Power Transistors 2SC3423

PACKAGE OUTLINE

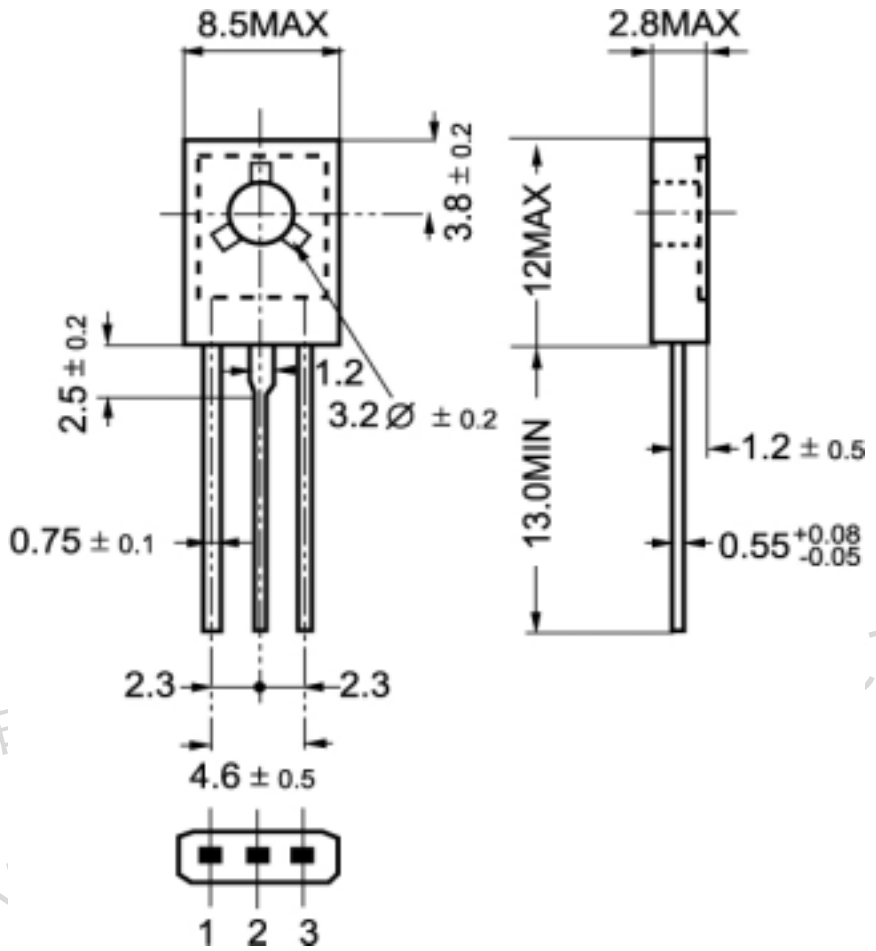

Fig.2 Outline dimensions

Silicon NPN Power Transistors 2SC3423

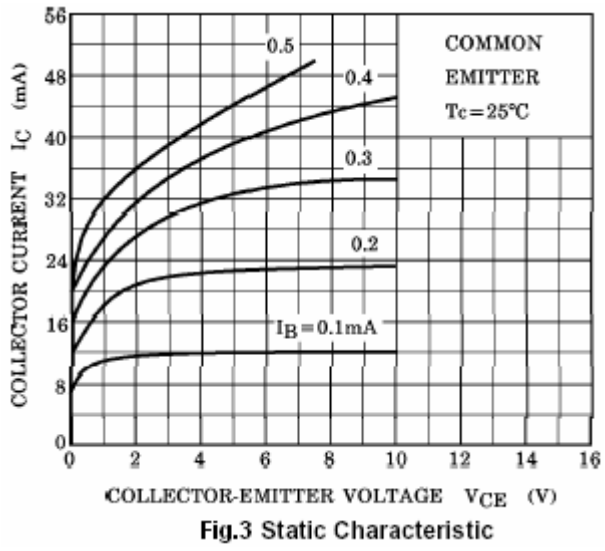

Fig.3 Static Characteristic

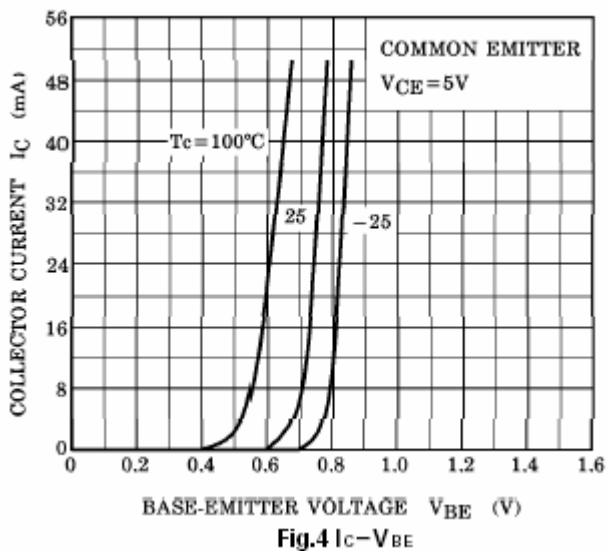

Fig.4 $I_C - V_{BE}$

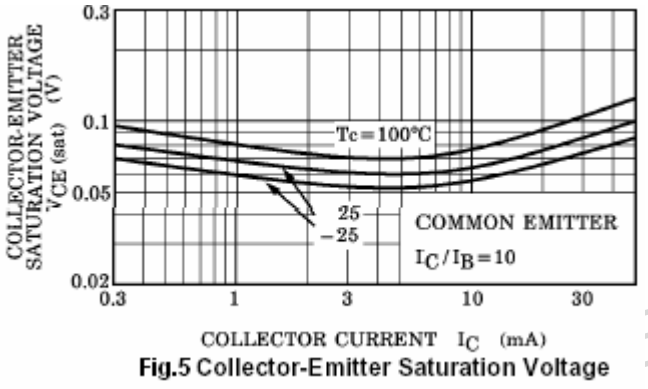

Fig.5 Collector-Emitter Saturation Voltage

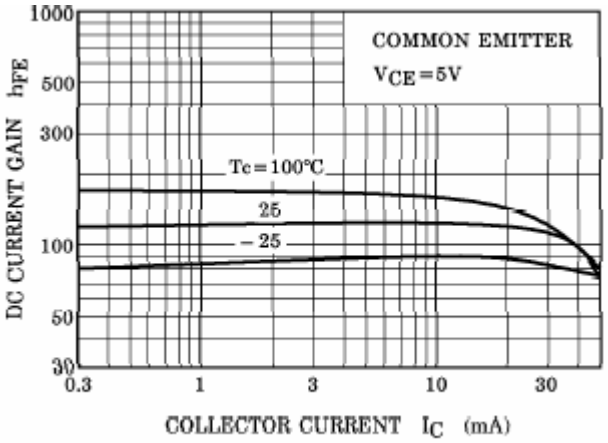

Fig.6 DC current Gain

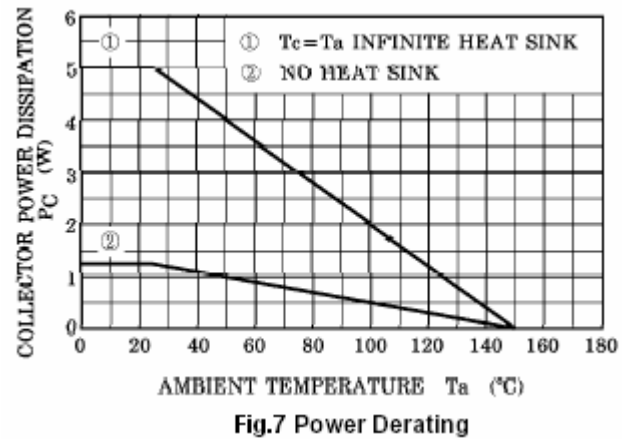

Fig.7 Power Derating